

## Refine Search

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### Search Results -

Terms	Documents
L13 and (("gate insulation" or "gate dielectric") near6 buried)	8

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**Database:**

US Pre-Grant Publication Full-Text Database
US Patents Full-Text Database
US OCR Full-Text Database
EPO Abstracts Database
JPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins

**Search:**

L17		
		Refine Search

  

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### Search History

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DATE: Wednesday, December 07, 2005    [Printable Copy](#)    [Create Case](#)

Set	Query	Hit Count	Set Name
side by side			result set
<i>DB=USPT; PLUR=YES; OP=OR</i>			
<u>L17</u>	L13 and (("gate insulation" or "gate dielectric") near6 buried)	8	<u>L17</u>
<u>L16</u>	L13 and ("bottom gate")	129	<u>L16</u>
<u>L15</u>	L13 and ("botom gate")	0	<u>L15</u>
<u>L14</u>	L13 and ((transistor near8 ((below or under or in) near5 buried)))	5	<u>L14</u>
<u>L13</u>	SOI and TFT	1133	<u>L13</u>
<u>L12</u>	"trench gate" same "channel stop"	10	<u>L12</u>
<u>L11</u>	JFET same ((gate or region) near5 (exten\$5) near7 (epitaxial or channel))	131	<u>L11</u>
<u>L10</u>	JFET same ((gate or region) near7 (exten\$5 or depth) near7 (epitaxial or channel))	186	<u>L10</u>
<u>L9</u>	JFET and ((gate or region) near7 (exten\$5 or depth) near7 (epitaxial or channel))	561	<u>L9</u>
<u>L8</u>	6031265 and (gate near15 JFET)	0	<u>L8</u>

<u>L7</u>	6031265 and ((source or drain) near15 JFET)	1	<u>L7</u>
<u>L6</u>	6031265 and ((source or drain) near7 JFET)	0	<u>L6</u>
<u>L5</u>	6855970 and source	1	<u>L5</u>
<u>L4</u>	L2 and problem\$ and depletion	1	<u>L4</u>
<u>L3</u>	L2 and problem\$	1	<u>L3</u>
<u>L2</u>	6855970 and trench	1	<u>L2</u>
<u>L1</u>	6031265 and JFET	1	<u>L1</u>

END OF SEARCH HISTORY